**Product data sheet** 

# 1. General description

Planar passivated four quadrant triac in a SOT82 (SIP3) plastic package intended for use in general purpose bidirectional switching and phase control applications.

### 2. Features and benefits

- · High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- · Less sensitive gate for improved noise immunity
- Triggering in all four quadrants
- Compact package

# 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{DRM}$	repetitive peak off-state voltage			8	00		V
$I_{T(RMS)}$	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 107 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	4		Α		
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; $t_p = 20 \text{ms}$ ; Fig. 4; Fig. 5	25		А		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	11	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 7}$	-	-	30	70	mA

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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	·/	
2	T2	main terminal 2		Ν
3	G	gate		T2 T1
mb	T2	mounting base; main terminal 2	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	G sym051
			1 2 3	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
BT134-800	SIP3	plastic single-ended package; 3-leads (in-line)	SOT82			

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking codes
BT134-800	BT134-800

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# 8. Limiting values

#### **Table 5. Limiting values**

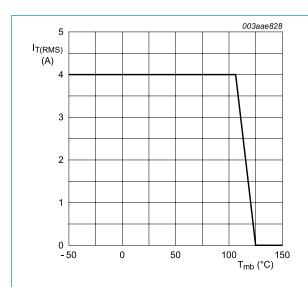
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 107 °C; <u>Fig 1</u> ; <u>Fig 2</u> ; <u>Fig 3</u>	4	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig 4; Fig 5	25	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	27	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>P</sub> = 10 ms; SIN	3.1	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 70 mA; T2+ G+	50	A/µs
		I <sub>G</sub> = 70 mA; T2+ G-	50	A/µs
		I <sub>G</sub> = 70 mA; T2- G-	50	A/µs
		I <sub>G</sub> = 140 mA; T2- G+	10	A/µs
I <sub>GM</sub>	peak gate current		2	Α
$P_GM$	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		125	°C

> 12 I<sub>T(RMS)</sub>

(A)

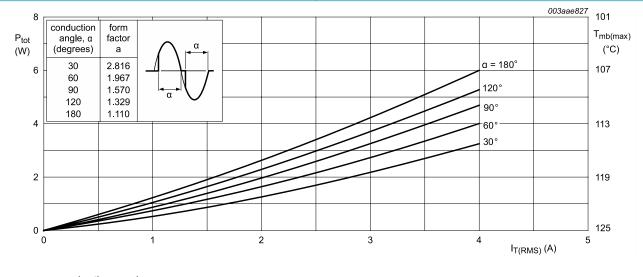
003aae830



10 8 6 4 2 0 L 10-2 10<sup>-1</sup> 10 surge duration (s)

Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

 $f = 50 \text{ Hz}; T_{mb} \le 107 \text{ }^{\circ}\text{C}$ Fig. 2. RMS on-state current as a function of surge duration; maximum values



 $\alpha$  = conduction angle

 $a = form \ factor = I_{T(RMS)} / I_{T(AV)} \\ Fig. \ 3. \quad Total \ power \ dissipation \ as \ a \ function \ of RMS \ on-state \ current; \ maximum \ values$ 

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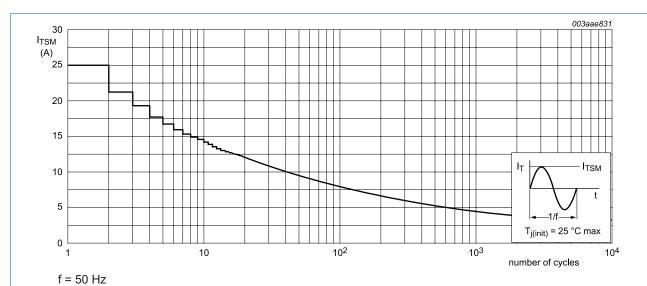
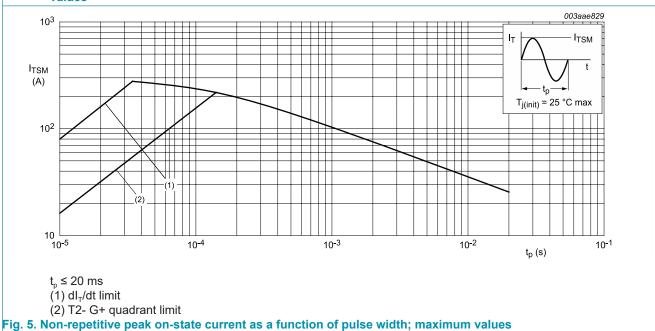


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance	half cycle; Fig 6	-	-	3.7	K/W
from junction to mounting base	full cycle; Fig 6	-	-	3	K/W	
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	100	-	K/W

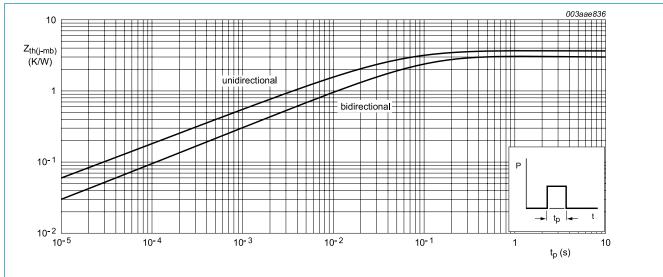


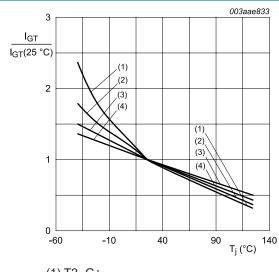
Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 ^{\circ}\text{C; } Fig. 7$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	11	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 7}$	-	30	70	mA
I <sub>L</sub>	latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 8$	-	7	20	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 8$	-	16	30	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	5	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	30	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	5	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	100	250	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 ^{\circ}\text{C}; dI_{com}/dt = 1.8 \text{ A/}$ ms; $I_T = 4 \text{ A};$ gate open circuit	-	50	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$V_D = 800 \text{ V}; I_{TM} = 6 \text{ A}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

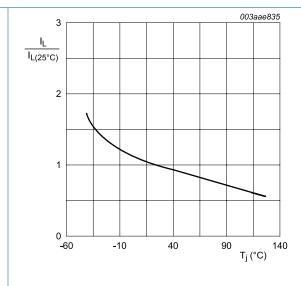


Fig. 8. Normalized latching current as a function of junction temperature

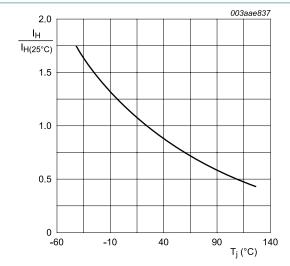
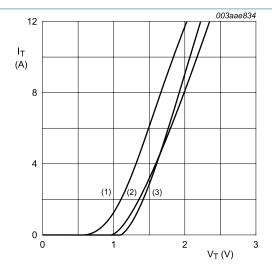


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.27 \text{ V}; R_s = 0.091 \Omega$
- (1) T<sub>i</sub> = 125 °C; typical values
- (2)  $T_i = 125$  °C; maximum values
- (3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

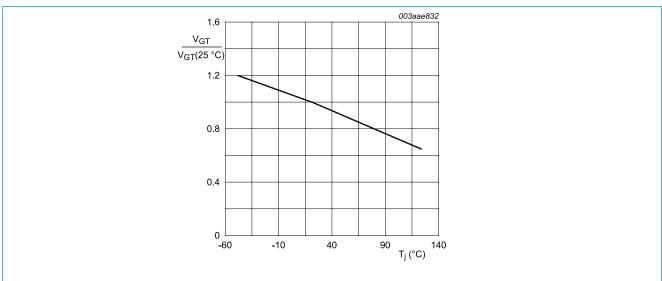
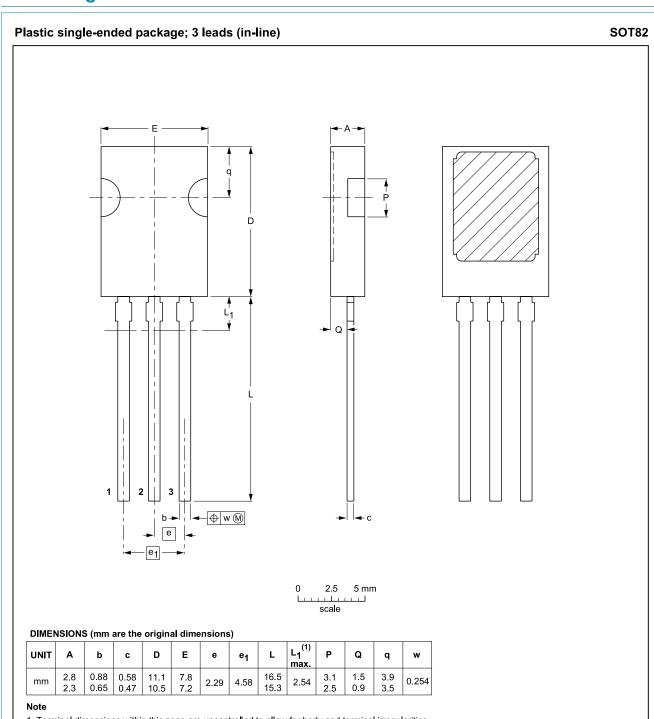


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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# 11. Package outline



1. Terminal dimensions within this zone are uncontrolled to allow for body and terminal irregularities.

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	ElAJ		PROJECTION	ISSUE DATE
SOT82						97-06-11

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## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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For more information, please visit: http://www.ween-semi.com
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